



30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

-45 A

Features

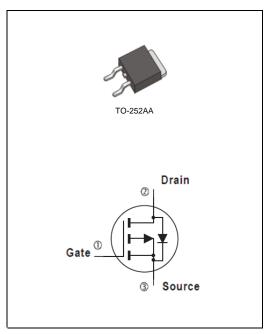
- $R_{DS(ON)}$, V_{GS} @-10V, I_D @-10A<15.5m Ω
- R_{DS(ON)}, V_{GS}@-4.5V,I_D@-6A<23mΩ
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std.. (Halogen Free)



• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	-30	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	l _D	-45	А	
	T _C =100°C		-28		
Pulsed Drain Current ^(Note 1)	T _C =25°C	I _{DM}	-180	ı	
Power Dissipation	T _C =25°C	Po	40	W	
	T _C =100°C		16		
Continuous Drain Current	T _A =25°C	I _D	-10	А	
	T _A =70°C		-8		
Power Dissipation	T _A =25°C	ſ	2.0	W	
Power Dissipation	T _A =70°C	Pb	1.3		
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	$R_{ heta JC}$	3.1	°C/W	
	Junction to Ambient	$R_{ heta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =-250uA	-30	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-1.0	-1.6	-2.5			
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V,I _D =-10A	-	12	15.5	mΩ		
		V_{GS} =-4.5V, I_{D} =-6A	-	18	23			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V,V _{GS} =0V	-	-	-1.0	uA		
Gate-Source Leakage Current	I _{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	<u>+</u> 100	nA		
Dynamic (Note 6)								
Total Gate Charge	Q_{g}	V_{DS} =-15V, I_{D} =-8A, V_{GS} =-4.5V ^(Note 1,2)	-	14	-	nC		
Gate-Source Charge	Q_gs		-	4.6	-			
Gate-Drain Charge	Q_gd		-	5.4	-			
Input Capacitance	Ciss	V _{DS} =-15V, V _{GS} =0V, f=1.0MHZ	-	1556	-	pF		
Output Capacitance	Coss		-	243	-			
Reverse Transfer Capacitance	Crss	I=1.0IVII IZ	-	175	-			
Turn-On Delay Time	td _(on)	\/ 45\/ 40	-	7.3	-			
Turn-On Rise Time	t _r	V_{DD} =-15V, I_{D} =-1A, V_{GS} =-10V, R_{G} =6 Ω (Note 1,2)	-	13	-	ns		
Turn-Off Delay Time	td _(off)		-	88	-			
Turn-Off Fall Time	t _f		-	48	-			
Drain-Source Diode								
Maximum Continuous Drain-Source	,		-	-	-45	А		
Diode Forward Current	I _S							
Diode Forward Voltage	V_{SD}	I _S =-1A,V _{GS} =0V	-	-0.7	-1.0	V		

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited
- 5. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

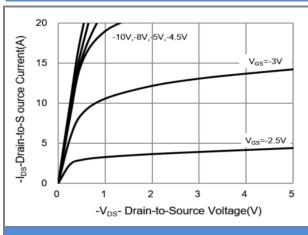


Fig.1 On-Region Characteristics

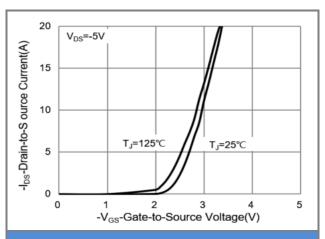


Fig.2 Transfer Characteristics

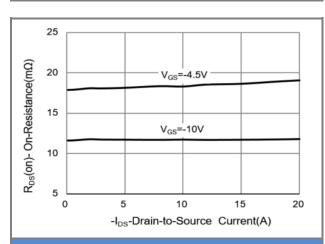


Fig.3 On-Resistance vs. Drain Current

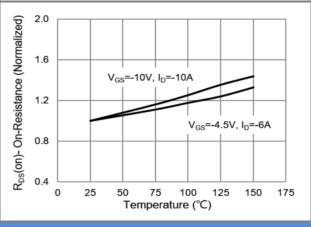


Fig.4 On-Resistance vs. Junction temperature

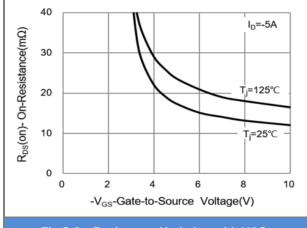


Fig.5 On-Resistance Variation with VGS.

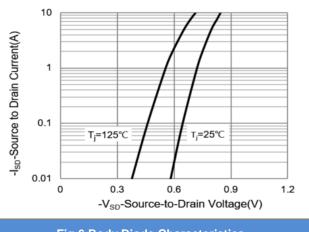


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

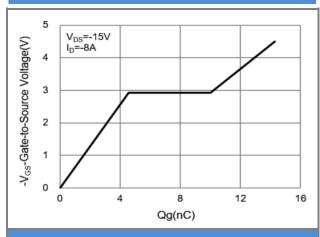


Fig.7 Gate-Charge Characteristics

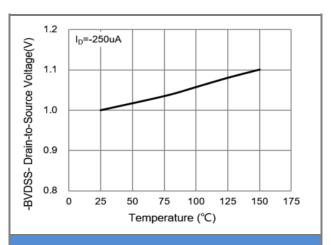


Fig.8 Breakdown Voltage Variation vs. Temperature

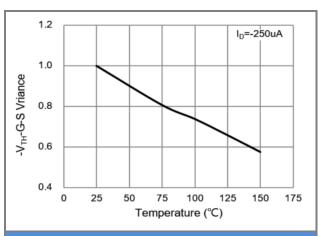


Fig.9 Threshold Voltage Variation with Temperature.

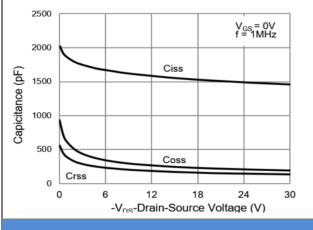


Fig.10 Capacitance vs. Drain-Source Voltage.

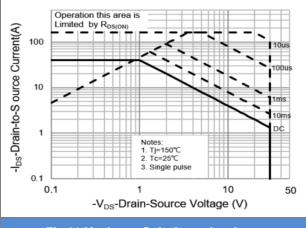


Fig.11 Maximum Safe Operating Area





TYPICAL CHARACTERISTIC CURVES

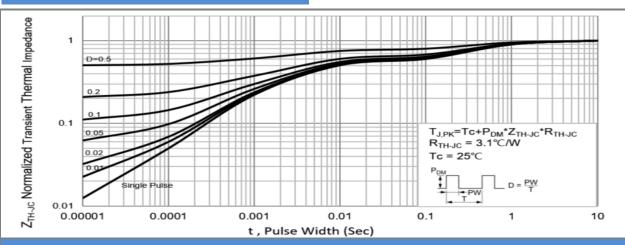
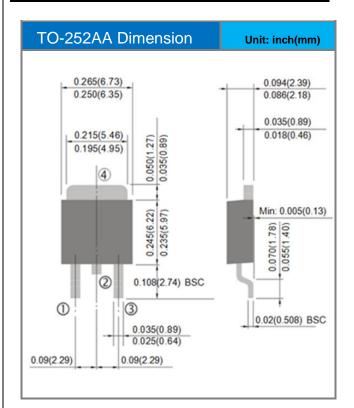


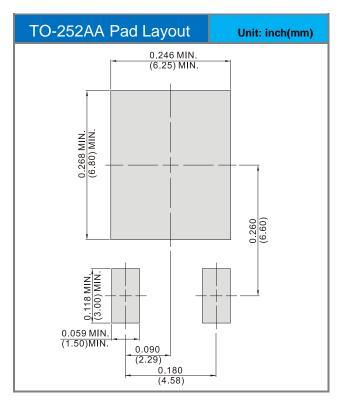
Fig.12 Normalized Thermal Transient Impedance





Packaging Information









PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD45P03_L2_00001	TO-252AA	3,000pcs / 13" reel	D45P03	Halogen free





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